

Diode Specifications

Type	IBM P/N	Type of Crystal	Maximum Forward Voltage Drop @ 25°C		Reverse Leakage Current @ 55°C		Reverse Recovery Time* (usec) @ 25°C
			$E_F(v)$	$I_F(ma)$	$E_B(v)$	$I_L(ua)$	
AA _s	491008	Ge	0.4	5.0	15.0	75.0	0.5-4.0
AF _s	492431	Ge	1.0	25.0	100.0	100.0	
AG _s	492457	Ge	0.5	5.0	50.0	125.0	
AL _s	2106333	Si	1.5	100.0	100.0	100.0	
AN	491007	Ge	1.0	3.0	15.0	150.0	
AR	419214	Si	1.1	200.0	50.0	75.0	
AS	491281	Ge	0.4	3.0	15.0	25.0	0.5
AU	491300	Si	1.0	100.0	40.0	10.0	1.5
F _s	503591	Ge	1.0	5.0	50.0	125.0	0.5-3.5
G _s	503592	Ge	1.0	5.0	50.0	250.0	0.5-3.5
J _s	492430	Ge	1.0	200.0	10.0	100.0	4.0
M	334908	Ge	1.0	40.0	10.0	20.0	4.0
P	333264	Ge	0.5	100.0	65.0	1200.0	
R	504361	Ge	1.0	40.0	10.0	20.0	4.0

* Recovery time is the time necessary for the diode to stop conducting after it has been passing current in the forward direction.